

## **Excellent Integrated System Limited**

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Intersil EL5027IWTZ-T7

For any questions, you can email us directly: <u>sales@integrated-circuit.com</u>



# intersil

Data Sheet

#### May 4, 2007

FN7426.1

EL5027

#### Dual 2.5MHz Rail-to-Rail Input-Output Buffer

The EL5027 is a dual, low power, high voltage rail-to-rail input-output buffer. Operating on supplies ranging from 5V to 15V, while consuming only 110 $\mu$ A per channel, the EL5027 has a bandwidth of 2.5MHz (-3dB). The EL5027 also provides rail-to-rail input and output ability, giving the maximum dynamic range at any supply voltage.

The EL5027 also features fast slewing and settling times, as well as a high output drive capability of 30mA (sink and source). These features make the EL5027 ideal for use as voltage reference buffers in Thin Film Transistor Liquid Crystal Displays (TFT-LCD). Other applications include battery power, portable devices, and anywhere low power consumption is important.

The EL5027 is available in space-saving 6 Ld TSOT package and operates over a temperature range of -40°C to +85°C.

### **Ordering Information**

PART NUMBER (Note)	PART MARKING	PACKAGE (Pb-free)	TAPE & REEL	PKG. DWG. #
EL5027IWTZ-T7	BVAA	6 Ld TSOT-23	7" (3k pcs)	MDP0049
EL5027IWTZ-T7A	BVAA	6 Ld TSOT-23	7" (250 pcs)	MDP0049

NOTE: Intersil Pb-free products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pbfree requirements of IPC/JEDEC J STD-020C.

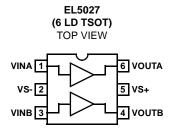
#### Features

- 2.5MHz -3dB bandwidth
- Unity gain buffer
- Supply voltage = 4.5V to 16.5V
- Low supply current (per buffer) = 110µA
- High slew rate = 1.2V/µs
- Rail-to-rail operation
- · Pb-free plus anneal available (RoHS compliant)

#### **Applications**

- TFT-LCD drive circuits
- Electronics notebooks
- · Electronics games
- Personal communication devices
- Personal Digital Assistants (PDA)
- Portable instrumentation
- Wireless LANs
- Office automation
- Active filters
- ADC/DAC buffer

#### Pinout



1



#### Absolute Maximum Ratings (T<sub>A</sub> = +25°C)

Supply Voltage between V <sub>S</sub> + and V <sub>S</sub> +18V
Input Voltage
Maximum Continuous Output Current
Maximum Die Temperature+125°C

#### **Thermal Information**

Storage Temperature	65°C to +150°C
Ambient Operating Temperature	40°C to +85°C
Power Dissipation	See Curves
Pb-free reflow profile	see link below
http://www.intersil.com/pbfree/Pb-FreeReflow.	asp

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

IMPORTANT NOTE: All parameters having Min/Max specifications are guaranteed. Typical values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore:  $T_J = T_C = T_A$ 

PARAMETER	DESCRIPTION	CONDITION	MIN	TYP	MAX	UNIT
INPUT CHARAC	CTERISTICS	·				
V <sub>OS</sub>	Input Offset Voltage	$V_{CM} = 0V$		1	15	mV
TCV <sub>OS</sub>	Average Offset Voltage Drift	(Note 1)		5		µV/°C
IB	Input Bias Current	V <sub>CM</sub> = 0V		2	50	nA
R <sub>IN</sub>	Input Impedance			1		GΩ
C <sub>IN</sub>	Input Capacitance			1.35		pF
A <sub>V</sub>	Voltage Gain	$-4.5V \le V_{OUT} \le 4.5V$	0.995		1.005	V/V
OUTPUT CHAR	ACTERISTICS				1	
V <sub>OL</sub>	Output Swing Low	I <sub>L</sub> = -5mA		-4.92	-4.85	V
V <sub>OH</sub>	Output Swing High	I <sub>L</sub> = 5mA	4.85	4.92		V
I <sub>SC</sub>	Short-circuit Current	Short to GND		±120		mA
POWER SUPPL	Y PERFORMANCE					
PSRR	Power Supply Rejection Ratio	$V_S$ is moved from ±2.25V to ±7.75V	55	80		dB
I <sub>S</sub>	Supply Current (Per Buffer)	No load		110	160	μA
DYNAMIC PERI	FORMANCE					
SR	Slew Rate (Note 2)	-4.0V $\leq$ V_OUT $\leq$ 4.0V, 20% to 80%	0.7	1.2		V/µs
t <sub>S</sub>	Settling to +0.1%	V <sub>O</sub> = 2V step		900		ns
BW	-3dB Bandwidth	$R_{L} = 10k\Omega, C_{L} = 10pF$		2.5		MHz
CS	Channel Separation	f = 5MHz		75		dB

NOTES:

1. Measured over the operating temperature range

2. Slew rate is measured on rising and falling edges



## $\label{eq:constraint} \textbf{Electrical Specifications} \quad \text{V}_{S}\text{+}=\text{+}5\text{V}, \text{ V}_{S}\text{-}=\text{0V}, \text{ R}_{L}=\text{10k}\Omega \text{ and } \text{C}_{L}=\text{10pF to }2.5\text{V}, \text{ T}_{A}=\text{+}25^{\circ}\text{C} \text{ Unless Otherwise Specified.}$

PARAMETER	DESCRIPTION	CONDITION	MIN	TYP	MAX	UNIT
INPUT CHARA	CTERISTICS			1		1
V <sub>OS</sub>	Input Offset Voltage	V <sub>CM</sub> = 2.5V		1	15	mV
TCV <sub>OS</sub>	Average Offset Voltage Drift	(Note 1)		5		µV/°C
IB	Input Bias Current	V <sub>CM</sub> = 2.5V		2	50	nA
R <sub>IN</sub>	Input Impedance			1		GΩ
C <sub>IN</sub>	Input Capacitance			1.35		pF
A <sub>V</sub>	Voltage Gain	$0.5 \le V_{OUT} \le 4.5V$	0.995		1.005	V/V
OUTPUT CHAR	ACTERISTICS		1			
V <sub>OL</sub>	Output Swing Low	I <sub>L</sub> = -5mA		80	150	mV
V <sub>OH</sub>	Output Swing High	I <sub>L</sub> = 5mA	4.85	4.92		V
I <sub>SC</sub>	Short-circuit Current	Short to GND		±120		mA
POWER SUPPI	LY PERFORMANCE		4	1		1
PSRR	Power Supply Rejection Ratio	$V_S$ is moved from 4.5V to 15.5V	55	80		dB
Is	Supply Current (Per Buffer)	No load		110	160	μA
DYNAMIC PER	FORMANCE			I.		
SR	Slew Rate (Note 2)	$1V \le V_{OUT} \le 4V$ , 20% to 80%	0.7	1.2		V/µs
t <sub>S</sub>	Settling to +0.1%	V <sub>O</sub> = 2V Step		900		ns
BW	-3dB Bandwidth	$R_{L} = 10k\Omega, C_{L} = 10pF$		2.5		MHz
CS	Channel Separation	f = 5MHz		75		dB

NOTES:

1. Measured over the operating temperature range

2. Slew rate is measured on rising and falling edges



## $\label{eq:constraint} \textbf{Electrical Specifications} \quad \text{V}_{S^+} = +15 \text{V}, \text{ V}_{S^-} = 0 \text{V}, \text{ R}_L = 10 \text{k} \Omega \text{ and } \text{C}_L = 10 \text{pF to } 7.5 \text{V}, \text{ T}_A = 25^\circ \text{C} \text{ unless otherwise specified}.$

PARAMETER	DESCRIPTION	CONDITION	MIN	TYP	MAX	UNIT
INPUT CHARA	CTERISTICS			1		1
V <sub>OS</sub>	Input Offset Voltage	V <sub>CM</sub> = 7.5V		1	15	mV
TCV <sub>OS</sub>	Average Offset Voltage Drift	(Note 1)		5		µV/°C
IB	Input Bias Current	V <sub>CM</sub> = 7.5V		2	50	nA
R <sub>IN</sub>	Input Impedance			1		GΩ
C <sub>IN</sub>	Input Capacitance			1.35		pF
A <sub>V</sub>	Voltage Gain	$0.5 \le V_{OUT} \le 14.5V$	0.995		1.005	V/V
OUTPUT CHAR	ACTERISTICS		ł	1	1	1
V <sub>OL</sub>	Output Swing Low	I <sub>L</sub> = -5mA		80	150	mV
V <sub>OH</sub>	Output Swing High	I <sub>L</sub> = 5mA	14.85	14.92		V
I <sub>SC</sub>	Short-circuit Current	Short to GND		±120		mA
POWER SUPPL	Y PERFORMANCE			I.		r
PSRR	Power Supply Rejection Ratio	$V_{\mbox{S}}$ is moved from 4.5V to 15.5V	55	80		dB
IS	Supply Current (Per Buffer)	No load		110	160	μA
DYNAMIC PER	FORMANCE			I		r
SR	Slew Rate (Note 2)	$1V \le V_{OUT} \le 14V$ , 20% to 80%	0.7	1.2		V/µs
t <sub>S</sub>	Settling to +0.1%	V <sub>O</sub> = 2V Step		900		ns
BW	-3dB Bandwidth	$R_{L} = 10k\Omega, C_{L} = 10pF$		2.5		MHz
CS	Channel Separation	f = 5MHz		75		dB

NOTES:

1. Measured over the operating temperature range

2. Slew rate is measured on rising and falling edges



## Typical Performance Curves

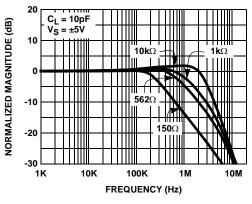


FIGURE 1. FREQUENCY RESPONSE FOR VARIOUS  $\mathsf{R}_\mathsf{L}$ 

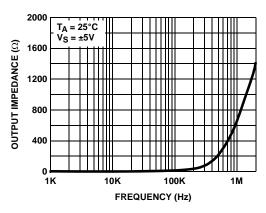


FIGURE 3. OUTPUT IMPEDANCE vs FREQUENCY

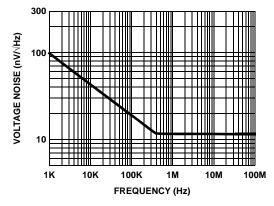


FIGURE 5. INPUT VOLTAGE NOISE SPECTRAL DENSITY vs FREQUENCY

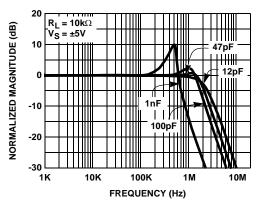


FIGURE 2. FREQUENCY RESPONSE FOR VARIOUS CL

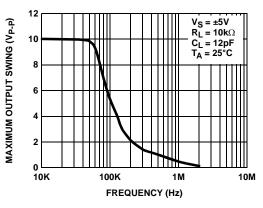


FIGURE 4. MAXIMUM OUTPUT SWING vs FREQUENCY

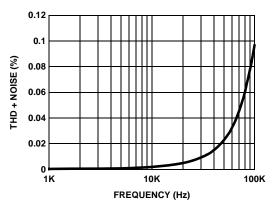
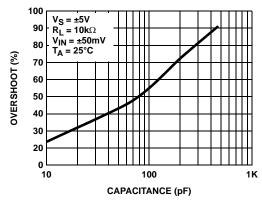


FIGURE 6. TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



## Typical Performance Curves (Continued)





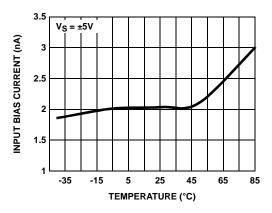


FIGURE 9. INPUT BIAS CURRENT vs TEMPERATURE

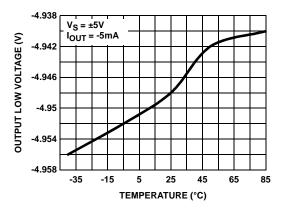


FIGURE 11. OUTPUT LOW VOLTAGE vs TEMPERATURE

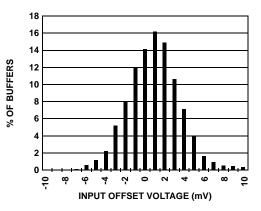


FIGURE 8. INPUT OFFSET VOLTAGE DISTRIBUTION

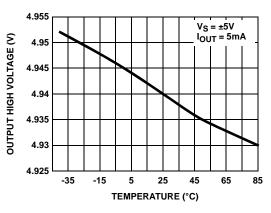


FIGURE 10. OUTPUT HIGH VOLTAGE vs TEMPERATURE

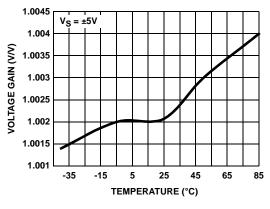


FIGURE 12. VOLTAGE GAIN vs TEMPERATURE



## Typical Performance Curves (Continued)

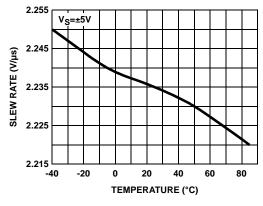


FIGURE 13. SLEW RATE vs TEMPERATURE

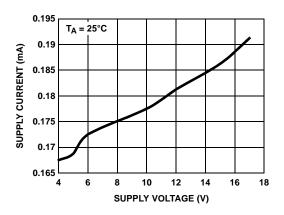


FIGURE 15. SUPPLY CURRENT PER CHANNEL vs SUPPY VOLTAGE

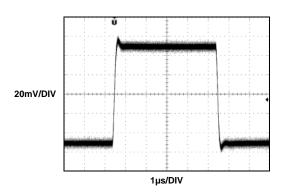


FIGURE 17. SMALL SIGNAL TRANSIENT RESPONSE

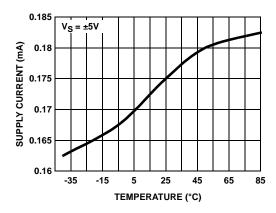


FIGURE 14. SUPPLY CURRENT PER CHANNEL vs TEMPERATURE

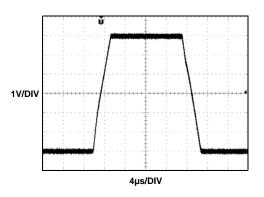


FIGURE 16. LARGE SIGNAL TRANSIENT RESPONSE



6 LD TSOT	PIN NAME	FUNCTION	EQUIVALENT CIRCUIT
1	VINA	Buffer A Input	V <sub>S</sub> +
2	VS-	Negative Supply Voltage	
3	VINB	Buffer B Input	(Reference Circuit 1)
4	VOUTB	Buffer B Output	······································
5	VS+	Positive Supply Voltage	
6	VOUTA	Buffer A Output	(Reference Circuit 2)

## **Pin Descriptions**

## Applications Information

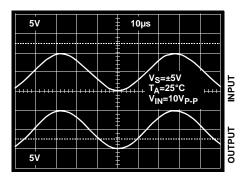
#### **Product Description**

The EL5027 unity gain buffer is fabricated using a high voltage CMOS process. It exhibits rail-to-rail input and output capability and has low power consumption (500 $\mu$ A per buffer). These features make the EL5027 ideal for a wide range of general-purpose applications. When driving a load of 10k $\Omega$  and 12pF, the EL5027 has a -3dB bandwidth of 2.5MHz and exhibits 2.2V/µs slew rate.

#### Operating Voltage, Input, and Output

The EL5027 is specified with a single nominal supply voltage from 5V to 15V or a split supply with its total range from 5V to 15V. Correct operation is guaranteed for a supply range of 4.5V to 16.5V. Most EL5027 specifications are stable over both the full supply range and operating temperatures of -40°C to +85°C. Parameter variations with operating voltage and/or temperature are shown in the typical performance curves.

The output swings of the EL5027 typically extend to within 80mV of positive and negative supply rails with load currents of 5mA. Decreasing load currents will extend the output voltage range even closer to the supply rails. Figure 1 shows the input and output waveforms for the device. Operation is from  $\pm$ 5V supply with a 10k $\Omega$  load connected to GND. The input is a 10V<sub>P-P</sub> sinusoid. The output voltage is approximately 9.985V<sub>P-P</sub>.



## FIGURE 18. OPERATION WITH RAIL-TO-RAIL INPUT AND OUTPUT

#### Short-Circuit Current Limit

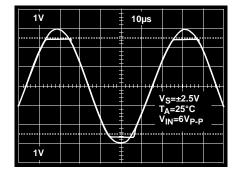
The EL5027 will limit the short-circuit current to  $\pm 120$ mA if the output is directly shorted to the positive or the negative supply. If an output is shorted indefinitely, the power dissipation could easily increase such that the device may be damaged. Maximum reliability is maintained if the output continuous current never exceeds  $\pm 30$ mA. This limit is set by the design of the internal metal interconnects.

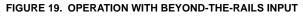
#### **Output Phase Reversal**

The EL5027 is immune to phase reversal as long as the input voltage is limited from V<sub>S</sub>- -0.5V to V<sub>S</sub>+ +0.5V. Figure 2 shows a photo of the output of the device with the input voltage driven beyond the supply rails. Although the device's



output will not change phase, the input's overvoltage should be avoided. If an input voltage exceeds supply voltage by more than 0.6V, electrostatic protection diodes placed in the input stage of the device begin to conduct and overvoltage damage could occur.





#### **Power Dissipation**

With the high-output drive capability of the EL5027 buffer, it is possible to exceed the +125°C 'absolute-maximum junction temperature' under certain load current conditions. Therefore, it is important to calculate the maximum junction temperature for the application to determine if load conditions need to be modified for the buffer to remain in the safe operating area.

The maximum power dissipation allowed in a package is determined according to:

$$\mathsf{P}_{\mathsf{DMAX}} = \frac{\mathsf{T}_{\mathsf{JMAX}} - \mathsf{T}_{\mathsf{AMAX}}}{\Theta_{\mathsf{JA}}}$$

where:

T<sub>JMAX</sub> = Maximum junction temperature

T<sub>AMAX</sub> = Maximum ambient temperature

 $\Theta_{JA}$  = Thermal resistance of the package

P<sub>DMAX</sub> = Maximum power dissipation in the package

The maximum power dissipation actually produced by an IC is the total quiescent supply current times the total power supply voltage, plus the power in the IC due to the loads, or:

$$\mathsf{P}_{\mathsf{DMAX}} = \Sigma i [\mathsf{V}_{\mathsf{S}} \times \mathsf{I}_{\mathsf{SMAX}} + (\mathsf{V}_{\mathsf{S}} + \mathsf{V}_{\mathsf{OUT}} i) \times \mathsf{I}_{\mathsf{LOAD}} i]$$

when sourcing, and:

$$\mathsf{P}_{\mathsf{DMAX}} = \Sigma i [\mathsf{V}_{\mathsf{S}} \times \mathsf{I}_{\mathsf{SMAX}} + (\mathsf{V}_{\mathsf{OUT}} i - \mathsf{V}_{\mathsf{S}}) \times \mathsf{I}_{\mathsf{LOAD}} i]$$

when sinking.

#### where:

- i = 1 to 2 for dual buffer
- V<sub>S</sub> = Total supply voltage
- I<sub>SMAX</sub> = Maximum supply current per channel
- V<sub>OUT</sub>i = Maximum output voltage of the application
- ILOADi = Load current

If we set the two  $P_{DMAX}$  equations equal to each other, we can solve for  $R_{LOAD}$  to avoid device overheat. Figure 20 and Figure 21 provide a convenient way to see if the device will overheat. The maximum safe power dissipation can be found graphically, based on the package type and the ambient temperature. By using the previous equation, it is a simple matter to see if  $P_{DMAX}$  exceeds the device's power derating curves.

#### **Unused Buffers**

It is recommended that any unused buffer have the input tied to the ground plane.

#### Driving Capacitive Loads

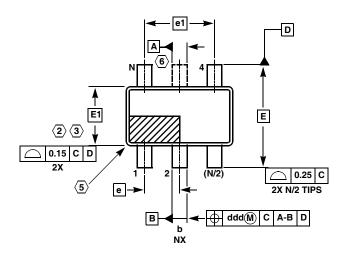
The EL5027 can drive a wide range of capacitive loads. As load capacitance increases, however, the -3dB bandwidth of the device will decrease and the peaking increase. The buffers drive 10pF loads in parallel with  $10k\Omega$  with just 1.5dB of peaking, and 100pF with 6.4dB of peaking. If less peaking is desired in these applications, a small series resistor (usually between  $5\Omega$  and  $50\Omega$ ) can be placed in series with the output. However, this will obviously reduce the gain slightly. Another method of reducing peaking is to add a "snubber" circuit at the output. A snubber is a shunt load consisting of a resistor in series with a capacitor. Values of  $150\Omega$  and 10nF are typical. The advantage of a snubber is that it does not draw any DC load current or reduce the gain.

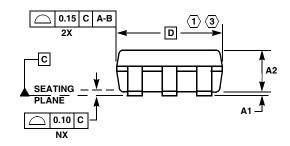
# Power Supply Bypassing and Printed Circuit Board Layout

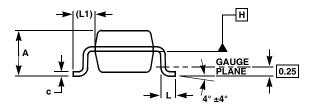
The EL5027 can provide gain at high frequency. As with any high frequency device, good printed circuit board layout is necessary for optimum performance. Ground plane construction is highly recommended, lead lengths should be as short as possible, and the power supply pins must be well bypassed to reduce the risk of oscillation. For normal single supply operation, where the V<sub>S</sub>- pin is connected to ground, a 0.1µF ceramic capacitor should be placed from V<sub>S</sub>+ to pin to V<sub>S</sub>- pin. A 4.7µF tantalum capacitor should then be connected in parallel, placed in the region of the buffer. One 4.7µF capacitor may be used for multiple devices. This same capacitor combination should be placed at each supply pin to ground if split supplies are to be used.



## TSOT Package Family







#### MDP0049

**TSOT PACKAGE FAMILY** 

	N			
SYMBOL	TSOT5	TSOT6	TSOT8	TOLERANCE
A	1.00	1.00	1.00	Max
A1	0.05	0.05	0.05	±0.05
A2	0.87	0.87	0.87	±0.03
b	0.38	0.38	0.29	±0.07
с	0.127	0.127	0.127	+0.07/-0.007
D	2.90	2.90	2.90	Basic
E	2.80	2.80	2.80	Basic
E1	1.60	1.60	1.60	Basic
е	0.95	0.95	0.65	Basic
e1	1.90	1.90	1.95	Basic
L	0.40	0.40	0.40	±0.10
L1	0.60	0.60	0.60	Reference
ddd	0.20	0.20	0.13	-
N	5	6	8	Reference
		·		Rev. B 2/07

NOTES:

- 1. Plastic or metal protrusions of 0.15mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.15mm maximum per side are not included.
- 3. This dimension is measured at Datum Plane "H".
- 4. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 5. Index area Pin #1 I.D. will be located within the indicated zone (TSOT6 AND TSOT8 only).
- 6. TSOT5 version has no center lead (shown as a dashed line).

All Intersil U.S. products are manufactured, assembled and tested utilizing ISO9000 quality systems. Intersil Corporation's quality certifications can be viewed at www.intersil.com/design/quality

Intersil products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design, software and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see www.intersil.com

